

BC546/547/548/549/550

Switching and Applications

- High Voltage: BC546, V_{CEO}=65V
 Low Noise: BC549, BC550
- Complement to BC556 ... BC560



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a =25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|------------------|-----------------------------------|-----------|-------|
| V _{CBO} | Collector-Base Voltage : BC546 | 80 | V |
| | : BC547/550 | 50 | V |
| | : BC548/549 | 30 | V |
| V _{CEO} | Collector-Emitter Voltage : BC546 | 65 | V |
| | : BC547/550 | 45 | V |
| | : BC548/549 | 30 | V |
| V _{EBO} | Emitter-Base Voltage : BC546/547 | 6 | V |
| | : BC548/549/550 | 5 | V |
| I _C | Collector Current (DC) | 100 | mA |
| I _C | Collector Power Dissipation | 500 | mW |
| T _J | Junction Temperature | 150 | °C |
| T _{STG} | Storage Temperature | -65 ~ 150 | °C |

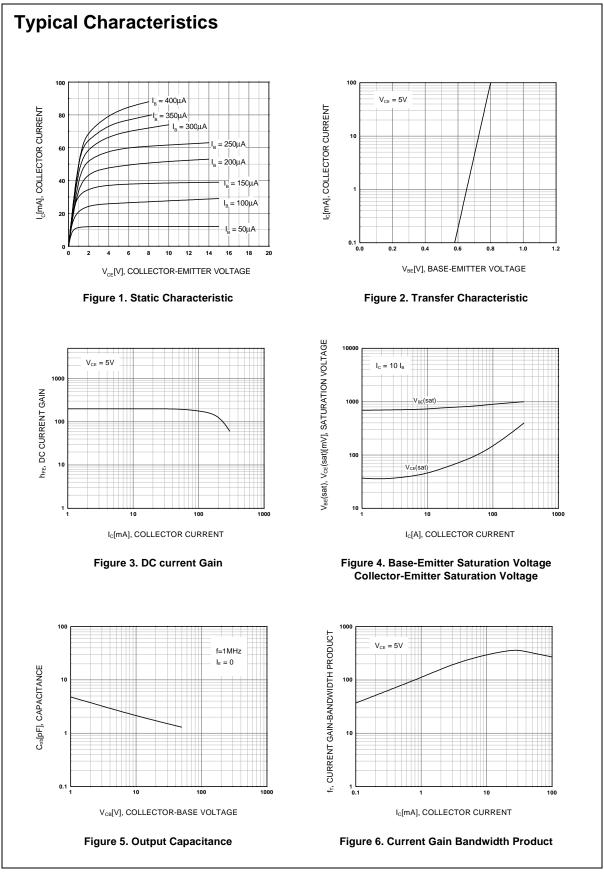
Electrical Characteristics T_a=25°C unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Тур. | Max. | Units |
|-----------------------|--------------------------------------|---|------|-------------------|-------------|----------------|
| I _{CBO} | Collector Cut-off Current | V_{CB} =30V, I_{E} =0 | | | 15 | nA |
| h _{FE} | DC Current Gain | V _{CE} =5V, I _C =2mA | 110 | | 800 | |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | I _C =10mA, I _B =0.5mA I _C =100mA, I _B =5mA | | 90 200 | 250 600 | mV mV |
| V _{BE} (sat) | Base-Emitter Saturation Voltage | I _C =10mA, I _B =0.5mA I _C =100mA, I _B =5mA | | 700 900 | | mV mV |
| V _{BE} (on) | Base-Emitter On Voltage | V_{CE} =5V, I_{C} =2mA V_{CE} =5V, I_{C} =10mA | 580 | 660 | 700 720 | mV mV |
| f _T | Current Gain Bandwidth Product | V _{CE} =5V, I _C =10mA, f=100MHz | | 300 | | MHz |
| C _{ob} | Output Capacitance | V _{CB} =10V, I _E =0, f=1MHz | | 3.5 | 6 | pF |
| C _{ib} | Input Capacitance | V _{EB} =0.5V, I _C =0, f=1MHz | | 9 | | pF |
| NF | Noise Figure : BC546/547/548 | V _{CE} =5V, I _C =200μA | | 2 | 10 | dB |
| | : BC549/550 : BC549 : BC550 | f =1KHz, R _G =2KΩ V_{CE} =5V, I _C =200 μ A R_{G} =2KΩ, f =30~15000MHz | | 1.2 1.4 1.4 | 4 4 3 | dB dB dB |

h_{FE} Classification

| Classification | А | В | С |
|-----------------|-----------|-----------|-----------|
| h _{FE} | 110 ~ 220 | 200 ~ 450 | 420 ~ 800 |

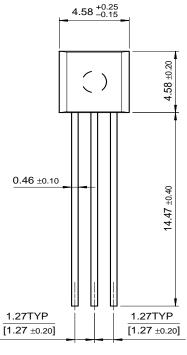
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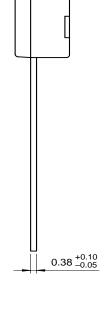


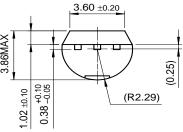
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Package Dimensions

TO-92







Dimensions in Millimeters

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| CoolFET™ | FASTr™ | MicroFET™ | PowerTrench [®] | SuperSOT™-6 |
| CROSSVOLT™ | FRFET™ | MicroPak™ | QFET™ | SuperSOT™-8 |
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|--------------------------|---------------------------|---|
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